

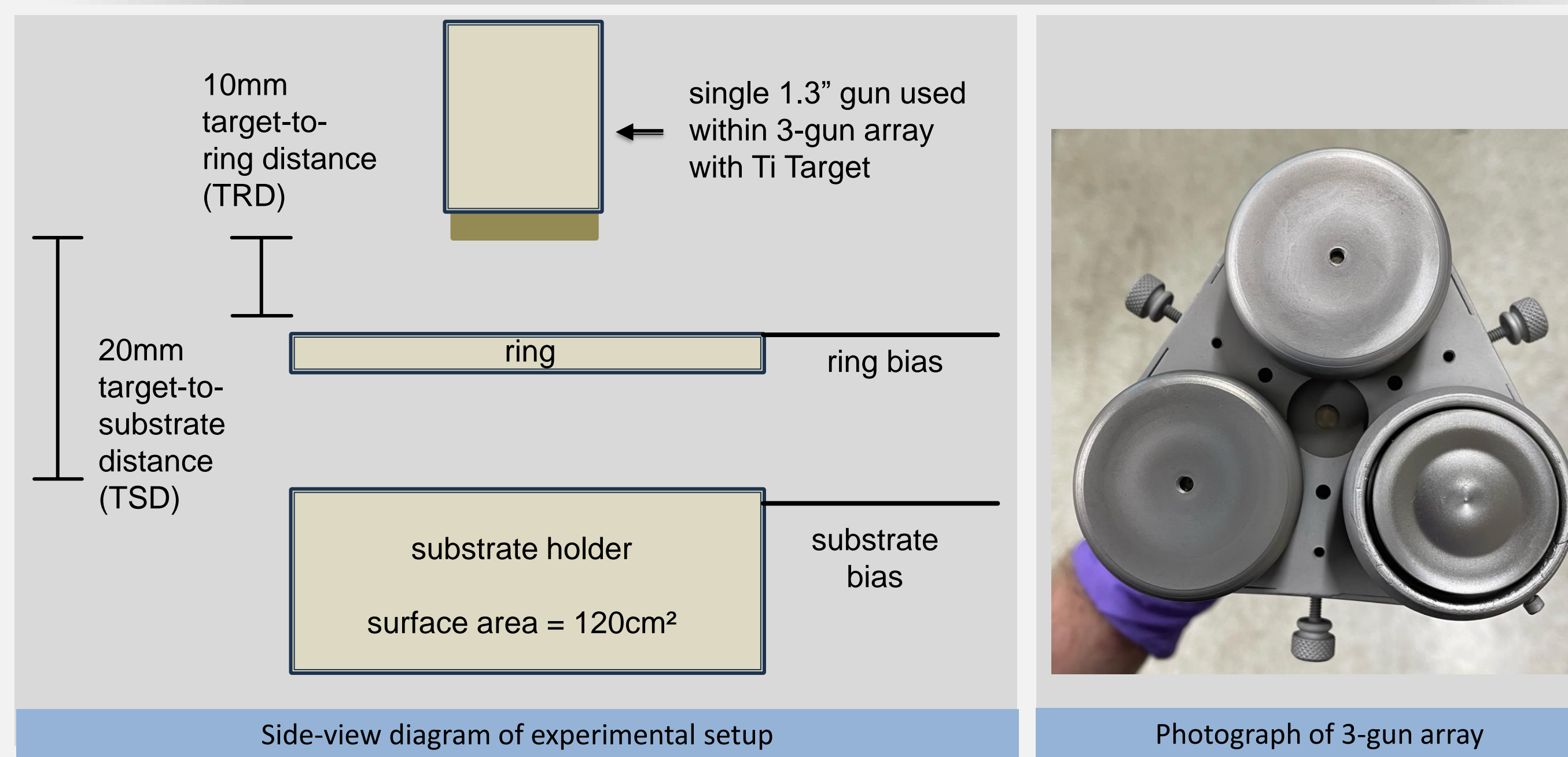
Investigation of Titanium as a Surrogate Material for Magnetron Sputtered Beryllium

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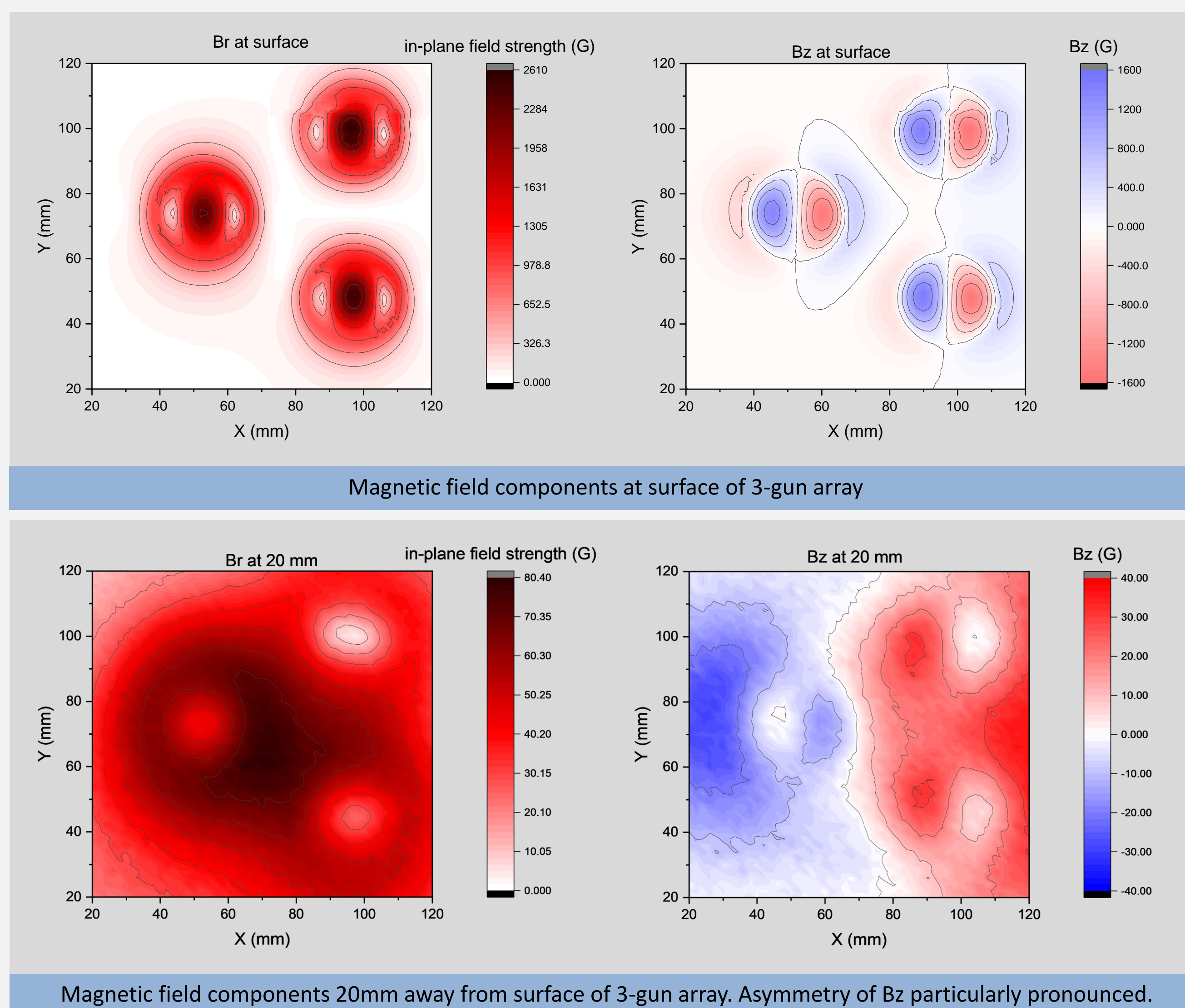
- The current chamber setup presents significant challenges for the deposition of Be. Hardware failures occur often and fixing them causes significant time delays and risk of contamination of capsules. Simplifying the process is, therefore, highly desirable, and utilizing HIPIMS is one way of achieving and improving this goal.
- Research and development of Be ablaters is impeded because of its toxicity. Thus, we use a non-toxic surrogate material with similar growth characteristics, comparable sputter yield, and reactivity.
- Here we investigate the use of Ti as a Be surrogate material. This work focuses on effects of direct current magnetron sputtering and high-power impulse magnetron sputtering parameters on I-V characteristics of the gun, ring, and substrate.

Characterizing Deposition Setup

Deposition Conditions with 3 Biased Electrodes



Mapping the Magnetic Field - 3-Gun Array Produces Asymmetrical Field

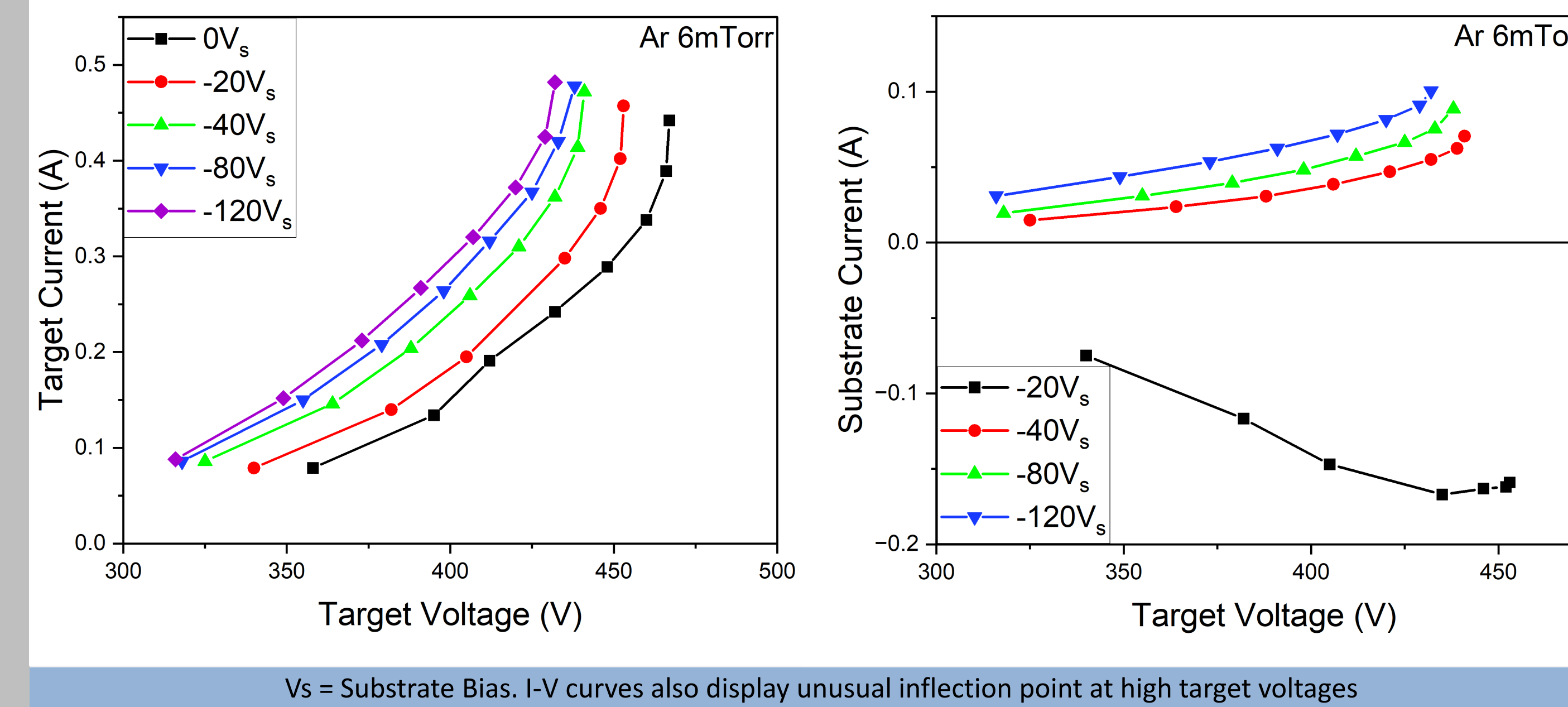


- Pan containing capsules is placed at 20mm TSD under typical deposition conditions.
 - At this distance capsules will experience differing plasma properties dependent on their position in the xy plane and which of the 3 guns are used.
 - A standard isolated MAK magnetron source has a cylindrically symmetric B field.

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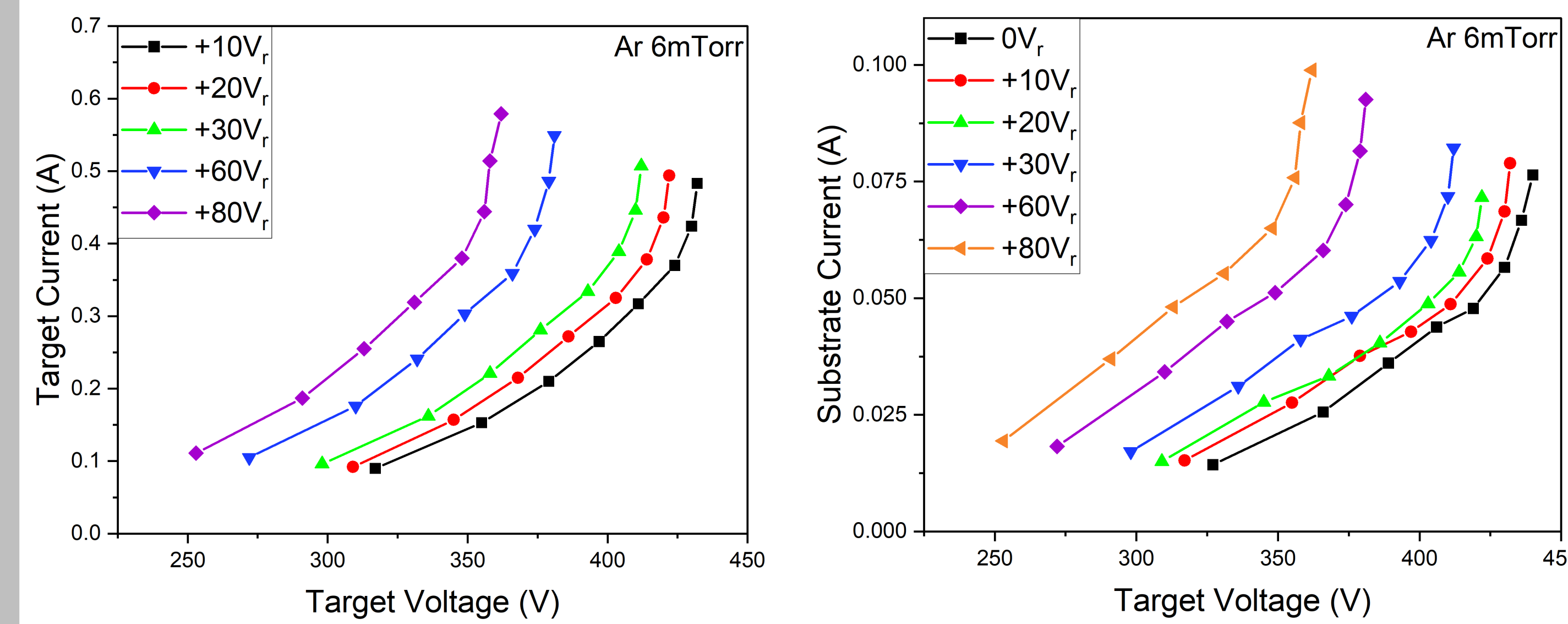
DC I-V Characteristics – No Ring Bias & Variable Substrate Bias

Increasingly Negative Substrate Bias Increases Target & Substrate Ion Current



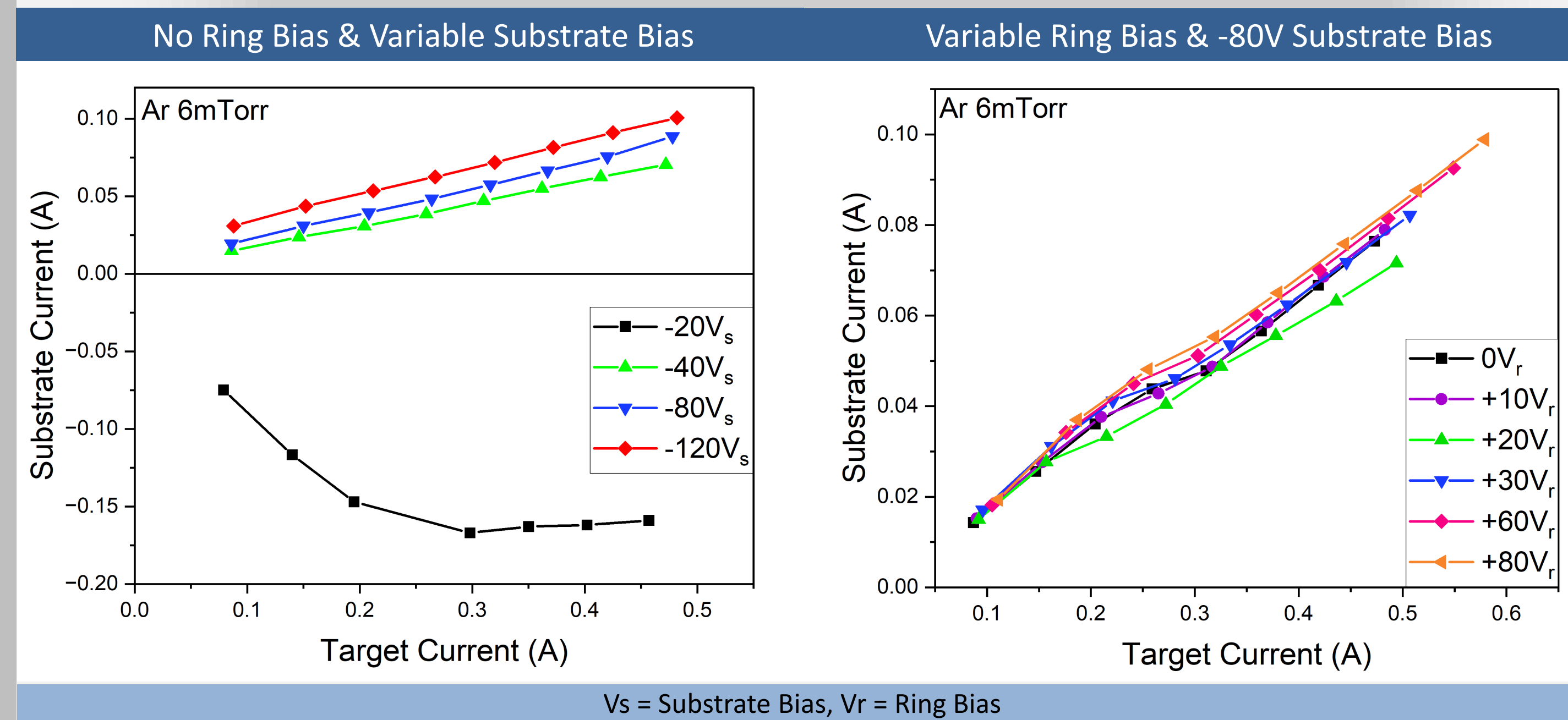
DC I-V Characteristics – Variable Ring Bias & -80V Substrate Bias

Increasingly Positive Ring Bias Increases Target & Substrate Ion Current Further



- Due to the inflection points, the I-V curves are not described by the classic Westwood and Thornton models.

Increasing Target Current Generally Produces Linear Increase in Substrate Current

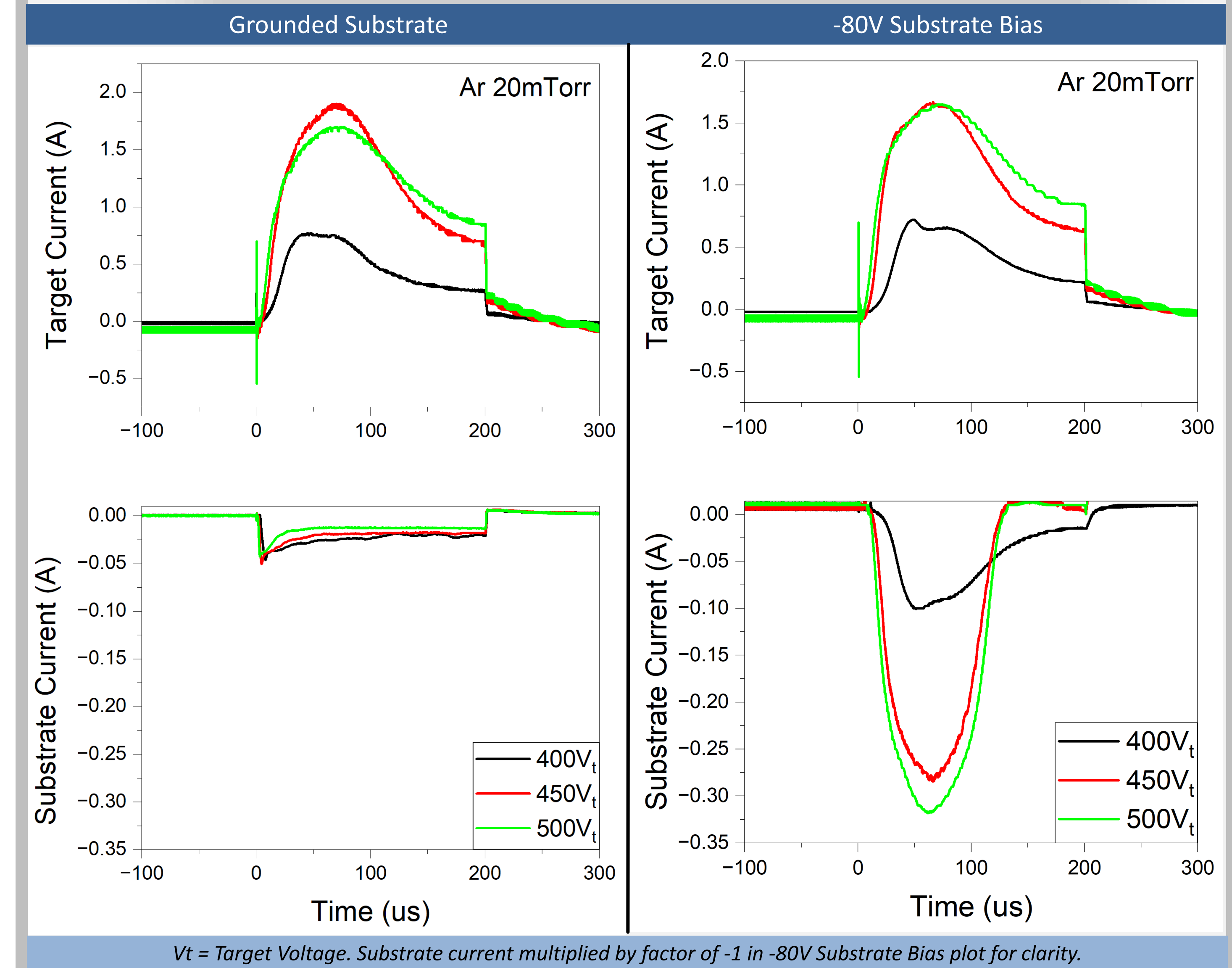


- 20V substrate bias with no ring bias acts as anode collecting.
- For all other substrate bias conditions, the substrate is an efficient ion collector

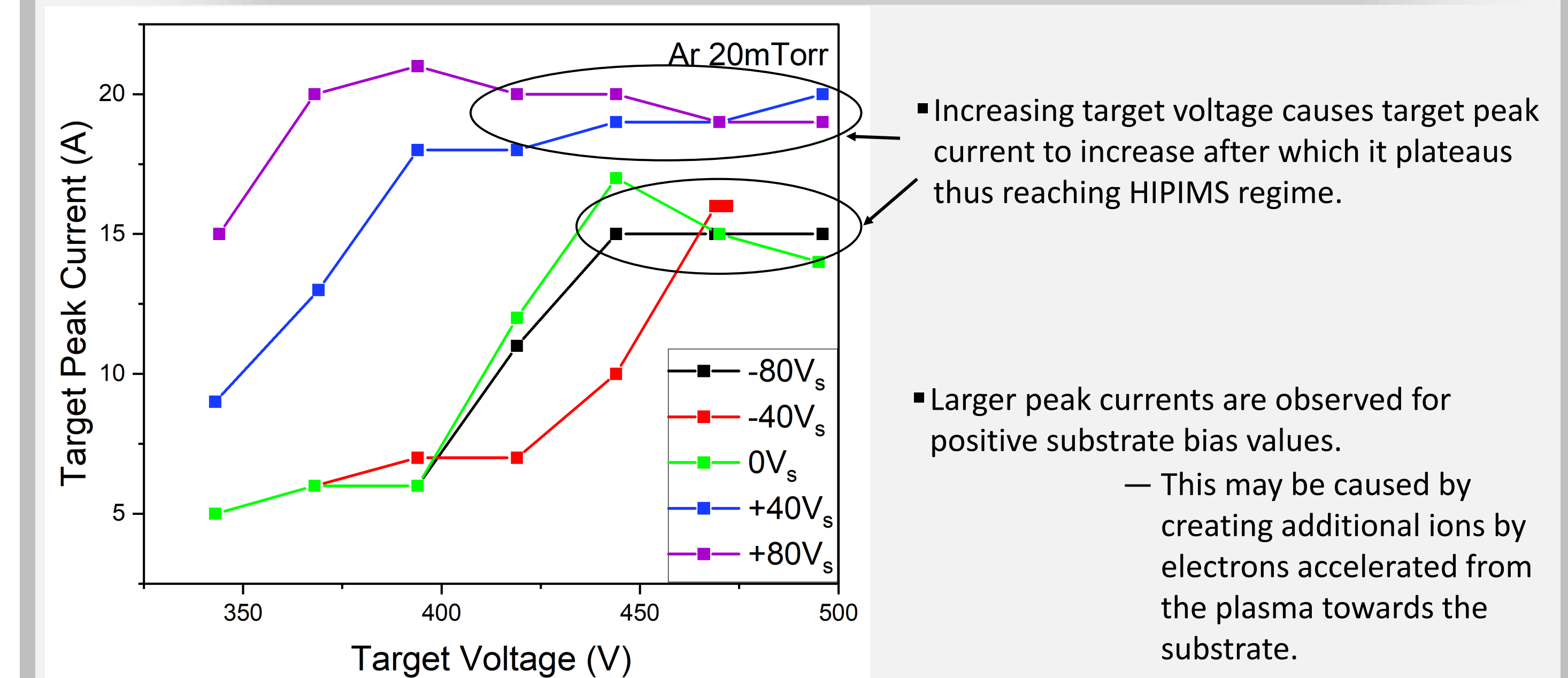
HIPIMS – No Ring Bias, Voltage Control Mode

- Unable to replicate low working pressure and voltage deposition conditions using HIPIMS.
 - Plasma difficult to ignite < 20mTorr working pressure. 20mTorr used.
 - Plasma difficult to ignite < 375V and very prone to arcing > 500V target voltage.
 - Magnetron source only rated to 375W average target power.
 - Voltage waveforms not affected by substrate bias – square wave.

Current Waveforms - Substrate Bias Significantly Increases Substrate Ion Current



Substrate Bias Significantly Affects Target Peak Current



Future Work

- Studying the target-to-ring distance's effect on the substrate current and I-V characteristics of the magnetron discharge.
- Using plasma diagnostic tools to correlate I-V characteristics with plasma properties.
- Leveraging our new understanding to identify deposition parameters for beryllium coatings.